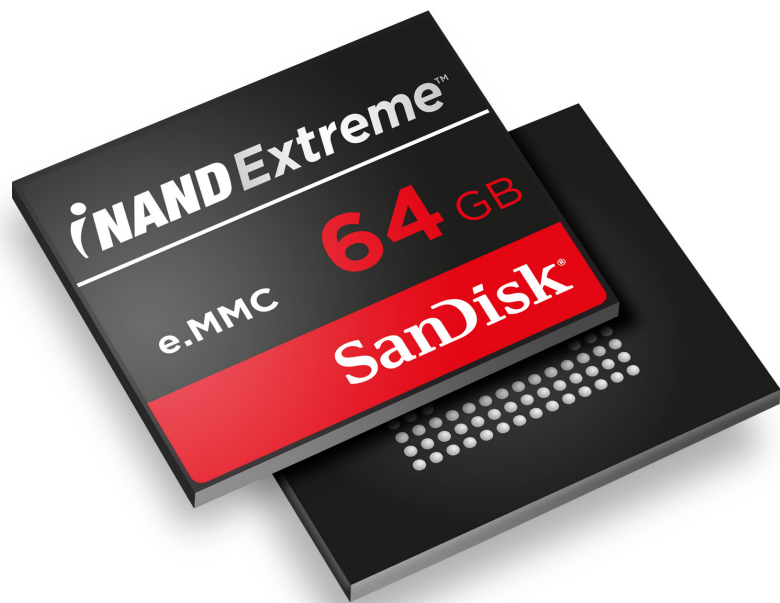


MWC: SanDisk Builds a Better iNAND Embedded Flash Drive

Ben Munson

SanDisk Corporation today announced the next generation of its iNAND Extreme embedded flash drive. Showing up so far in capacities up to in 64GB, iNAND Extreme presents a new



architecture designed to optimize performance on smartphones under more and more pressure from muscular processors, high-resolution cameras and strenuous applications like 4K video.

Built for Android devices, the new iNAND Extreme adheres to the latest e.MMC 5.0 specifications and incorporates a dual-core design. The idea is to lower latency and raise bandwidth.

iNAND Extreme also now incorporates an error correction mechanism, which enhances storage endurance, better equipping it to handle fragmentation and other issues that slow down performance over the life cycle of a device, particularly as the memory fills up.

Using the HS400 specification, the iNAND Extreme has increased its sequential write/read speeds up to 80/300 Mbps and its random write/read speeds up to 3000/6000 IOPS.

Rafael Feitelberg, senior director of marketing management at SanDisk, said the

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updates boost throughput in the memory to 1.5x of the host.

“This whole architecture is built such that it enables a tremendous amount of housekeeping on the memory that works in the background to enable a better user experience,” Feitelberg said, highlighting housekeeping functions like reorganizing data and error correction.

The new iNAND Extreme is now built on SanDisk’s 1Y nanometer process technology, which can put 64GB of storage in a form factor 11.5mm x 13mm in size and as thin as 1 mm.

General availability of new iNAND Extreme will begin in the second quarter of 2014.

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